## Amendments to the Abstract

## Please amend the Abstract of the Disclosure as follows:

A chemical vapor deposition (CVD) method apparatus for depositing a silicide and a CVD system for performing the same are is disclosed. After a substrate is loaded in a load-lock chamber, the substrate is transferred into a processing chamber. A silicide is deposited on [[a]] the substrate. After the substrate is transferred into the load-lock chamber, Residual residual gases remaining from the depositing step on the substrate are purged out by flowing air including H<sub>2</sub>O (g) from an air purge line connected to the load-lock chamber. to substantially remove fumes caused by the residual gases. The purged residual gases are exhausted by a vacuum pump connected to the air purge line. In the purge step, the cycle purge is carried out at the conditions similar to the flow of atmosphere, to substantially remove the fumes.